MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MC54/74HC03

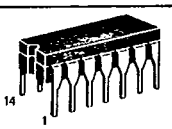
Quad 2-Input NAND Gate with Open-Drain Outputs

High-Performance Silicon-Gate CMOS

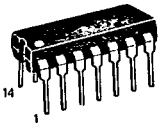
The MC54/74HC03 is identical in pinout to the LS03. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC03 NAND gate has, as its output, a high-performance MOS N-Channel transistor. This NAND gate can, therefore, with a suitable pullup resistor, be used in wired-AND applications. Having the output characteristic curves given in this data sheet, this device can be used as an LED driver or in any other application that only requires a sinking current.

- Output Drive Capability: 10 LSTTL Loads with Suitable Pullup Resistor
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 28 FETs or 7 Equivalent Gates



J SUFFIX
CERAMIC
CASE 632-08



N SUFFIX
PLASTIC
CASE 646-06

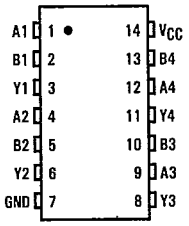
D SUFFIX
SOIC
CASE 751A-02

ORDERING INFORMATION

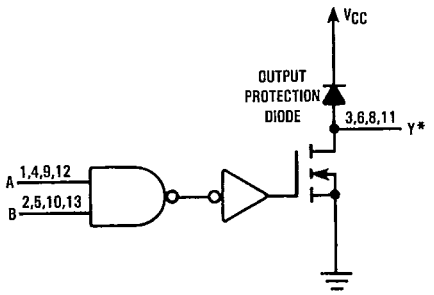
MC74HCXXN	Plastic
MC54HCXXJ	Ceramic
MC74HCXXD	SOIC

$T_A = -55°$ to 125°C for all packages.
Dimensions in Chapter 7.

PIN ASSIGNMENT



LOGIC DIAGRAM



PIN 14 = V_{CC}
PIN 7 = GND

*Denotes open-drain outputs.

FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	Z
L	H	Z
H	L	Z
H	H	L

Z = High Impedance

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MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	−0.5 to +7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	−1.5 to V_{CC}+1.5	V
V_{out}	DC Output Voltage (Referenced to GND)	−0.5 to V_{CC}+0.5	V
I_{in}	DC Input Current, per Pin	±20	mA
I_{out}	DC Output Current, per Pin	±25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±50	mA
P_D	Power Dissipation in Still Air, Plastic or Ceramic DIP†	750	mW
	SOIC Package†	500	
T_{stg}	Storage Temperature	−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		°C
	(Plastic DIP or SOIC Package)	260	
	(Ceramic DIP)	300	

*Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: −10 mW/°C from 65° to 125°C
Ceramic DIP: −10 mW/°C from 100° to 125°C
SOIC Package: −7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 4.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		−55	+125	°C
t_r, t_f	Input Rise and Fall Time	V_{CC}=2.0 V	0	1000	ns
	(Figure 1)	V_{CC}=4.5 V	0	500	
		V_{CC}=6.0 V	0	400	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				25°C to −55°C	≤85°C	≤125°C	
V_{IH}	Minimum High-Level Input Voltage	V_{out}=0.1 V, I_{out}=0 μA or V_{out}=V_{CC}−0.1 V, R_{pu} per Figure 2	2.0	1.5	1.5	1.5	V
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V_{IL}	Maximum Low-Level Input Voltage	V_{out}=0.1 V, I_{out}=0 μA or V_{out}=V_{CC}−0.1 V, R_{pu} per Figure 2	2.0	0.3	0.3	0.3	V
			4.5	0.9	0.9	0.9	
			6.0	1.2	1.2	1.2	
V_{OL}	Maximum Low-Level Output Voltage	V_{in}=V_{IH} or V_{IL} |I_{out}| ≤20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		V_{in}=V_{IH} or V_{IL} |I_{out}| ≤4.0 mA	4.5	0.26	0.33	0.40	
		|I_{out}| ≤5.2 mA	6.0	0.26	0.33	0.40	
I_{in}	Maximum Input Leakage Current	V_{in}=V_{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{in}=V_{CC} or GND, I_{out}=0 μA	6.0	2	20	40	μA
I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State, V_{in}=V_{IL} or V_{IH}, V_{out}=V_{CC} or GND	6.0	±0.5	±5.0	±10.0	μA

NOTE: Information on typical parametric values can be found in Chapter 4.

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AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			25°C to −55°C	≤85°C	≤125°C	
t_{PLZ}, t_{PZL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0 4.5 6.0	125 25 21	155 31 26	190 38 32	ns
t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C_{in}	Maximum Input Capacitance	—	10	10	10	pF
C_{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	—	10	10	10	pF

NOTES:
1. For propagation delays with loads other than 50 pF, see Chapter 4.
2. Information on typical parametric values can be found in Chapter 4.

C_{PD}	Power Dissipation Capacitance (Per Gate) Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ For load considerations, see Chapter 4.	Typical @ 25°C, V_{CC} = 5.0 V 8	pF

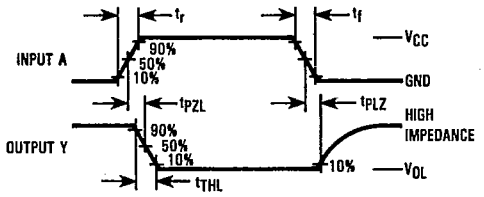
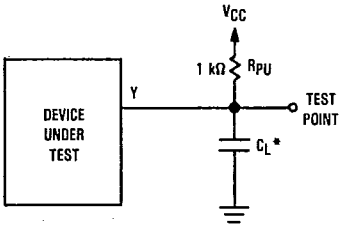
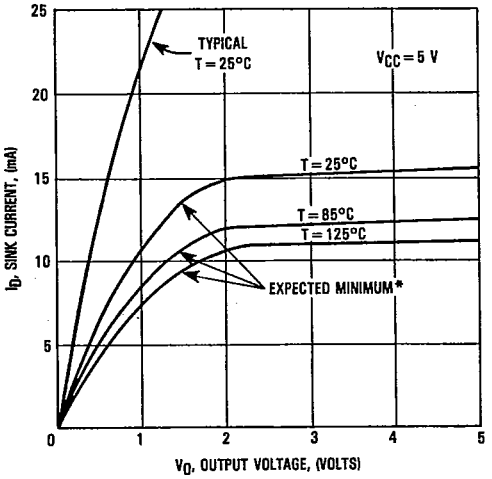


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance.

Figure 2. Test Circuit



*The expected minimum curves are not guarantees, but are design aids.

Figure 3. Open-Drain Output Characteristics

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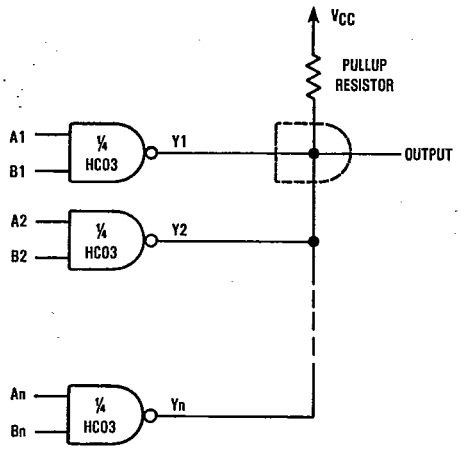
TYPICAL APPLICATIONS

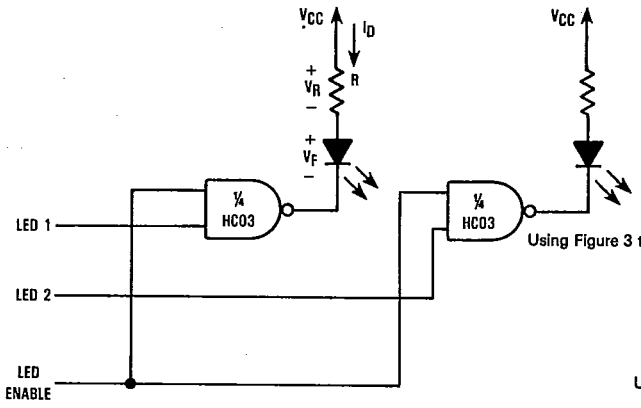
Wired AND



Output = Y1•Y2•...•Yn

$= \overline{A1B1 \bullet A2B2 \bullet \ldots \bullet AnBn}$

LED Driver with Blanking



Design Example

Conditions: $I_D \cong 10$ mA

Using Figure 3 typical curve, @ $I_D = 10$ mA, $V_{DS} \cong 0.4$ V

$$\therefore R = \frac{V_{CC} - V_F - V_O}{I_D}$$

$$= \frac{5\text{ V} - 1.7\text{ V} - 0.4\text{ V}}{10\text{ mA}}$$

$= 290\ \Omega$

Use R = 270 Ω